

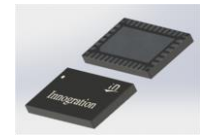


GaN HEMT 28V, 2450MHz 60W, RF Power Transistor

XTAH25055C6

Description

The XTAH25055C6 is a 60W GaN HEMT, designed for ISM/RF Energy application at 2.45GHz. The transistor is available in a highly cost effective 10*6mm, surface mount, QFN package with 100% production test to ensure the quality and consistency. It can be used in CW, Pulse and any other modulation modes. It is also the dual path version of 2 pcs of XTAH25032C6 integrated into the same package.



There is no guarantee of performance when this part is used in applications designed Outside of these frequencies.

- Typical Class AB RF Performance with device soldered through high density and plated grounding vias
Vds = 28V, Vgs=-2.54V, CW

Freq (MHz)	P1dB (dBm)	P1dB Gain(dB)	P3dB (dBm)	P3dB (W)	P3dB Eff(%)
2400	47.56	17.51	48.20	66.08	77.45
2450	47.32	17.66	48.09	64.41	77.20
2500	47.00	17.13	47.96	62.50	76.47

Applications

- S band power amplifier
- ISM/RF Energy power amplifier

Important Note: Proper Biasing Sequence for GaN HEMT Transistors

Turning the device ON

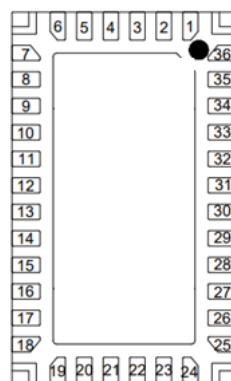
1. Set VGS to the pinch-off (VP) voltage, typically -5 V
2. Turn on VDS to nominal supply voltage
3. Increase VGS until IDS current is attained
4. Apply RF input power to desired level

Turning the device OFF

1. Turn RF power off
2. Reduce VGS down to VP, typically -5 V
3. Reduce VDS down to 0 V
4. Turn off VGS

Figure 1: Pin Connection definition

Transparent top view (Backside grounding for source)



Pin No.	Symbol	Description
8,9,10,11,14,15,16,17	RF IN/Vgs	RF Input, Vgs bias
26,27,28,29,32,33,34,35	RF OUT/VDD	RFOutput, Drain bias
Rest Pins and Package Base	GND	DC/RF Ground. Must be soldered directly to heatsink or copper coin for CW application.



Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain--Source Voltage	V_{DSS}	+150	Vdc
Gate--Source Voltage	V_{GS}	-8 to +0.5	Vdc
Operating Voltage	V_{DD}	36	Vdc
Maximum gate current	I_{gs}	16	mA
Storage Temperature Range	T_{stg}	-65 to +150	°C
Case Operating Temperature	T_c	+150	°C
Operating Junction Temperature	T_J	+225	°C

Table 2. Thermal Characteristics

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case by FEA $T_c = 85^\circ\text{C}$, at $P_{diss} = 20\text{W}$	$R_{\theta JC}$	1.95	°C /W

Table 3. Electrical Characteristics (TA = 25°C unless otherwise noted)

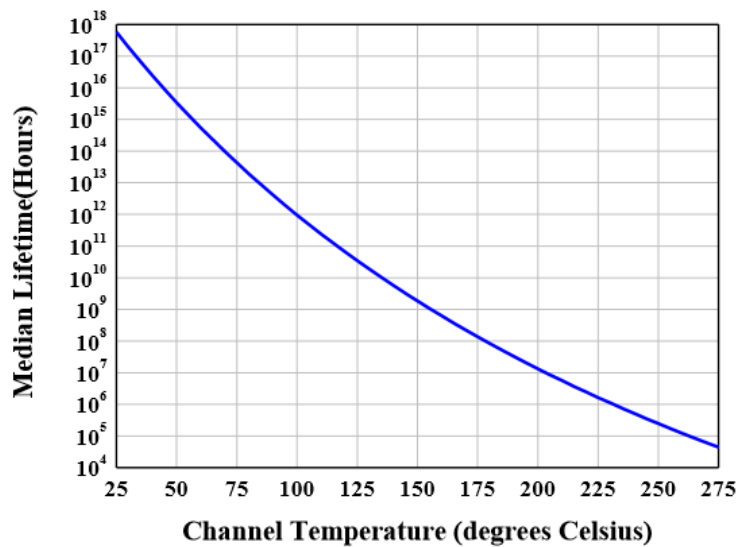
DC Characteristics (main path, measured on wafer prior to packaging)

Characteristic	Conditions	Symbol	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{GS} = -8\text{V}$; $I_{DS} = 16\text{mA}$	V_{DSS}		200		V
Gate Threshold Voltage	$V_{DS} = 10\text{V}$, $I_D = 16\text{mA}$	$V_{GS(th)}$	-4		-2	V
Gate Quiescent Voltage	$V_{DS} = 28\text{V}$, $I_{DS} = 30\text{mA}$, Measured in Functional Test	$V_{GS(Q)}$		-2.6		V

Ruggedness Characteristics

Characteristic	Conditions	Symbol	Min	Typ	Max	Unit
Load mismatch capability	2.5GHz, $P_{out} = 60\text{W}$ Pulsed CW All phase, No device damages	VSWR		10:1		

Figure 2: Median Lifetime vs. Channel Temperature





Typical performance

Figure 3: Efficiency and power gain as function of Pout

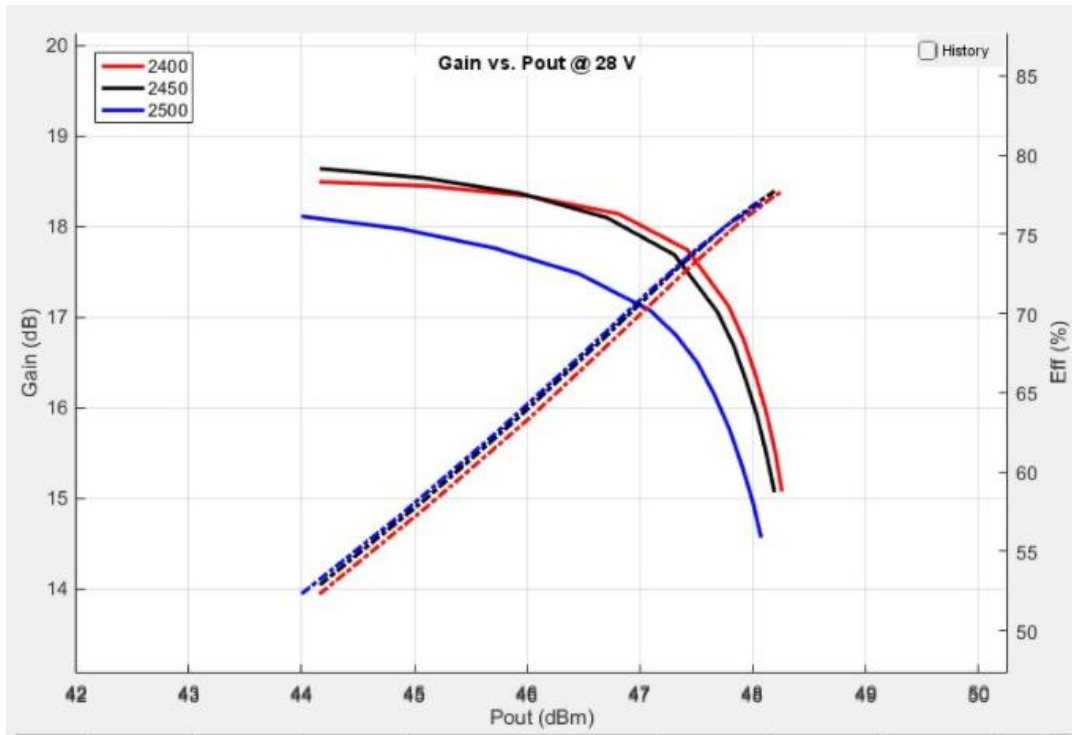


Figure 5: Network analyzer output S11/S21

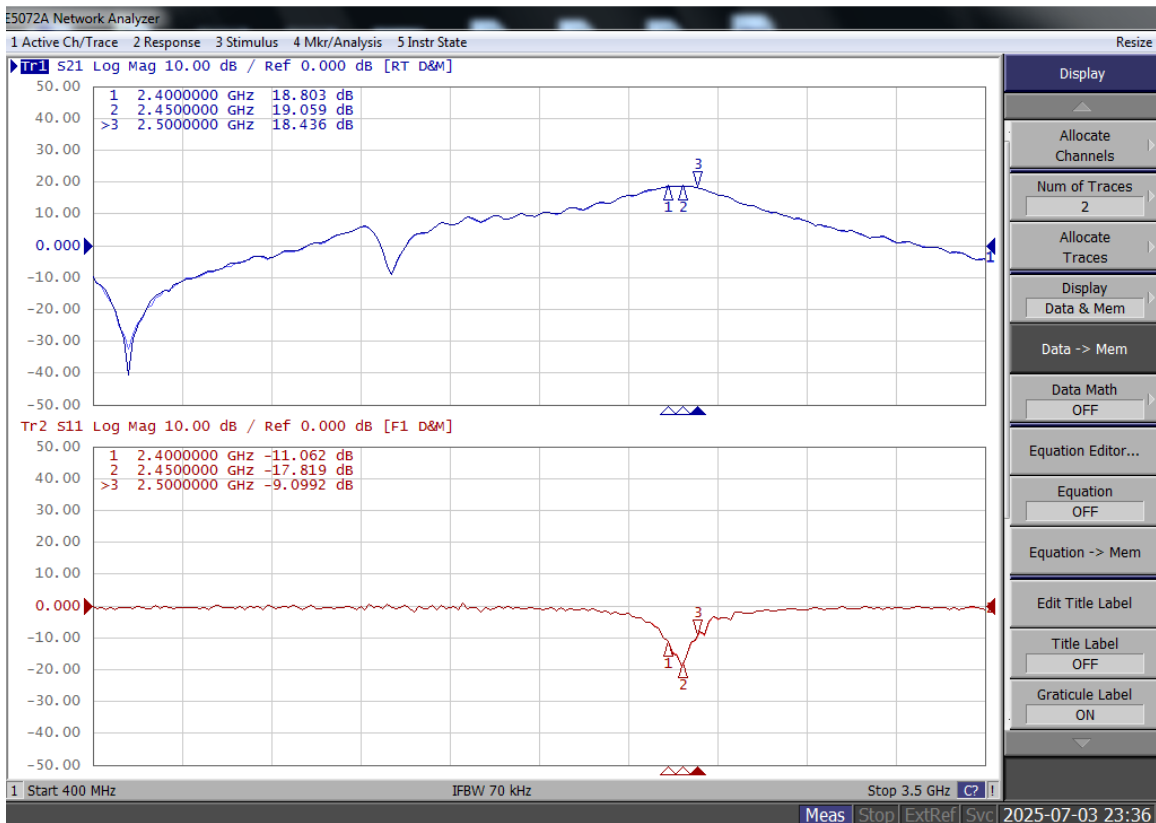
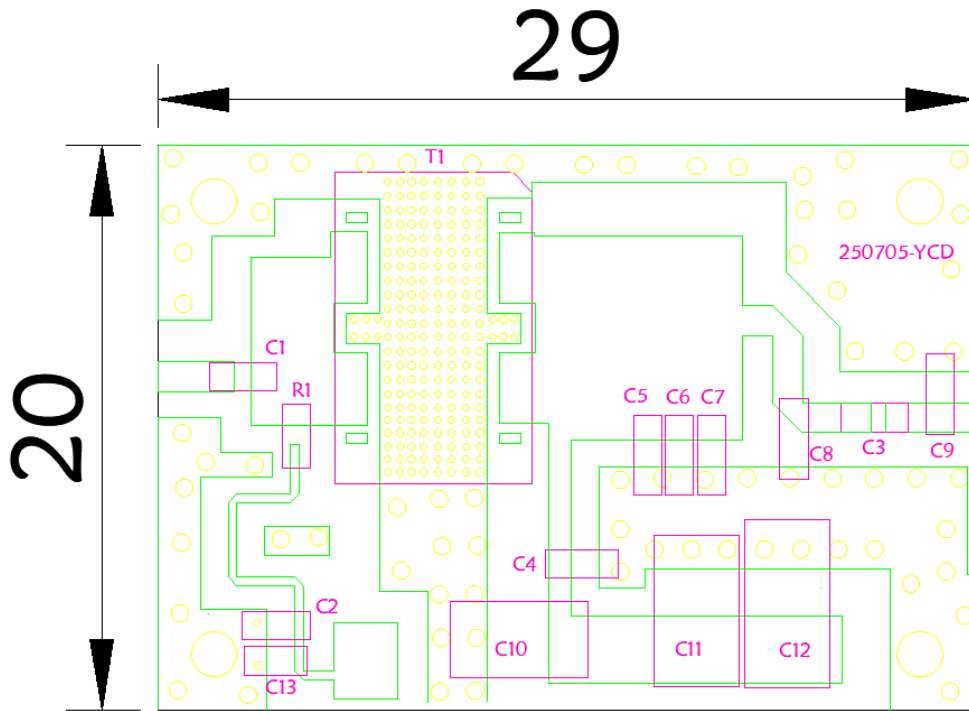


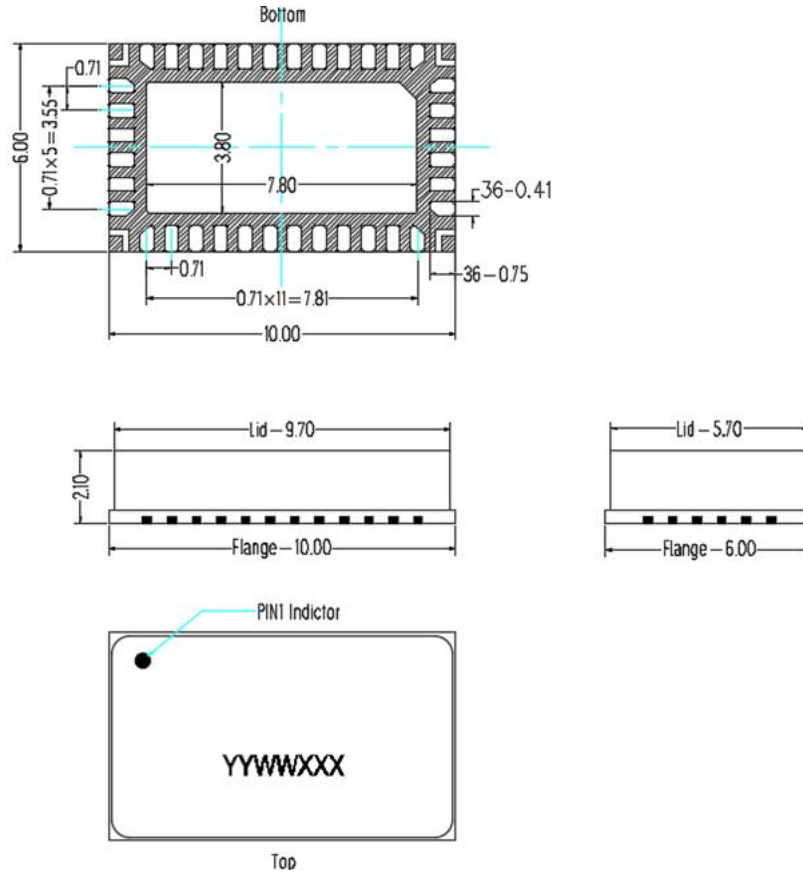
Figure 5: Picture of application board



Designator	Footprint	Comment	Quantity
C1, C2, C3, C4	0603	12 pF HIGH Q	4
C10,C11,C12,C13	1210	10uF/100V	4
C5,C6	0603	1.2 pF HIGH Q	2
C7	0603	0.2pF HIGH Q	1
C8	0603	0.6pF HIGH Q	1
C9	0603	0.7pF HIGH Q	1
R1	0603	10R	1
T1		XTAH25055C6	1



Table 4. Bill of materials of application board (PCB layout upon request, RO4350B 20mils) 10*6 Plastic Package



Notes:

1. All dimensions are in mm;
2. The tolerances unless specified are ± 0.2 mm.

Revision history

Table 4. Document revision history

Date	Revision	Datasheet Status
2025/7/4	V1.0	Preliminary Datasheet Creation

Application data based on: LWH-25-29

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